

Description

The HCJ3139K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 V_{DS} = -20V I_D =-0.66A R_{DS(ON)} < 560 mQ@ V_{GS}= -4.5V ESD Rating: 1500V HBM

Application

Load/Power Switching Interfacing Switching Battery Management for Ultra Small Portable Electronics

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
НСЈ3139К	SOT-723	KD	8000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±10	V
Ι _D	Drain Current-Continuous	-0.66	A
Ідм	Drain Current-Pulsed (Note 1)	-1.2	A
PD	Maximum Power Dissipation	0.15	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	850	°C /W





P-Channel MOSFET



Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250µA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±10	μA
Gate threshold voltage (note2)	V _{GS(th)}	V _{DS} =VGS, I _D =-250µA	-0.4	-0.7	-1.0	V
	R _{DS(on)}	V _{GS} =-4.5V, I _D =-0.5A			0.56	Ω
Drain-source on-resistance (note2)		V _{GS} =-2.5V, I _D =-0.2A			0.78	Ω
Maximum Continuous Drain to Source Diode Forward Current	Is				-0.6	А
Maximum Pulsed Drain to Source Diode Forward Current	I _{SM}				-1.2	А
Diode forward voltage	V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V
Input capacitance	Ciss			115		pF
Output capacitance	Coss	V _{DS} =-16V,V _{GS} =0V, f =1MHz		15		pF
Reverse transfer capacitance	Crss			9		pF
Turn-on delay time (note3)	t _{d(on)}	V _{GS} =-4.5V,V _{DS} =-10V, I _D =-200mA,R _{GEN} =10Ω		9		nS
Turn-on rise time (note3)	tr			6		nS
Turn-off delay time (note3)	t _{d(off)}			33		nS
Turn-off fall time (note3)	t _f			22		nS

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.

2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

3. Switching characteristics are independent of operating junction temperatures.

4. Guaranteed by design, not subject to producting.



SOT-723 Package Outline Dimensions





Symbol	Dimensions In Millimet		
Symbol	Min	Max	
А	0.42	0.50	
A1	0.00	0.05	
b	0.16	0.28	
b1	0.25	0.35	
с	0.07	0.16	
D	1.10	1.30	
е	0.8TYP		
E	1.10	1.30	
E1	0.75	0.85	
θ	8°	10º	



Suggested Pad Layout (mm)





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